

# Multi 10 kW short pulse CO<sub>2</sub> laser development for HVM-EUVL

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## Abstract

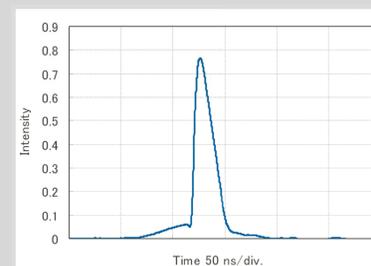
The solution for HVM EUV lithography is a laser produced plasma light source with a cost effective CO<sub>2</sub> drive laser and a Sn target. To demonstrate this we developed a RF-excited CO<sub>2</sub> laser MOPA system with an output power of 8 kW at a pulse length of 20 ns at 100 kHz repetition rate. The laser has a very good beam quality and wave front aberration is therefore no limitation at all contrary to solid state laser.

## High-Power Short-Pulse RF-excited CO<sub>2</sub> Laser for EUV Lithography



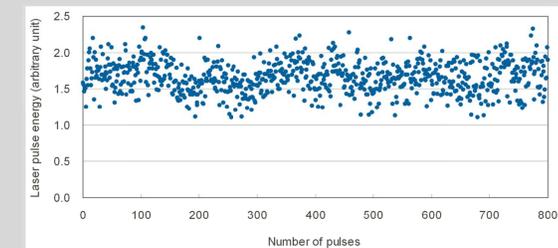
High Power and short pulse RF-excited MOPA CO<sub>2</sub> laser for LPP EUV light source

## Output laser beam characteristics of the CO<sub>2</sub> MOPA system



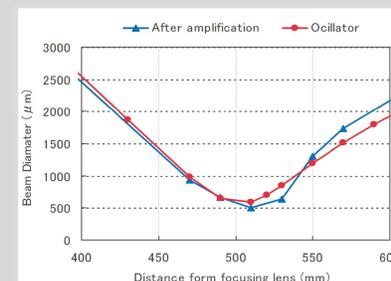
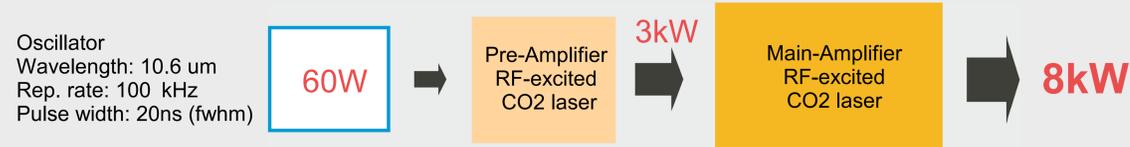
Temporal pulse shape of the amplified output pulse. Pulse duration is 20 ns(FWHM). Pedestal component is below 10%.

## CO<sub>2</sub> laser pulse stability



Output laser pulse energy stability : 2% (3sigma, 500 pulse)

## Block Diagram of MOPA CO<sub>2</sub> laser system



Dependence of focused beam diameter on the distance from the focusing lens. There is no significant change after amplification.

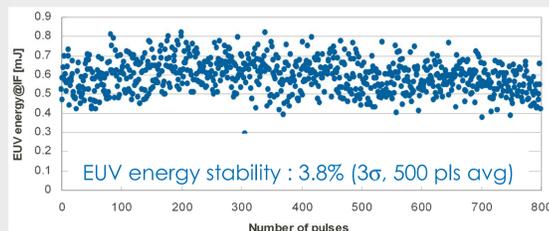
## Development of 20 kW short-pulse RF-excited MOPA CO<sub>2</sub> laser system



Multi-line Oscillator  
 Rep. rate: 100 kHz  
 Pulse width: 20ns (fwhm)

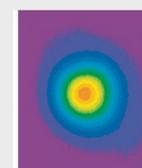
## EUV generation from high power CO<sub>2</sub> laser produced Sn plasma

EUV pulse energy (in-band) at intermediate focus



EUV energy stability : 3.8% (3σ, 500 pls avg)

IF image (in-band EUV)



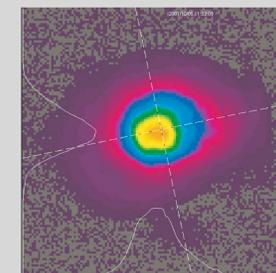
size :  
 3.6 mm (H),  
 3.3 mm (V) at 1/e<sup>2</sup>



1/3 pi sr collector (120 deg)

Target : Rotating Sn plate, Laser irradiation power: 6.5 kW (100 kHz, 20 ns)

In-band EUV at IF: **60 W** (4 sr collector), 16 W measured (1/3 pi sr mirror)



Beam profile of the laser output. M2 was 1.1

## Conclusion

- High-power and short-pulse RF-excited CO<sub>2</sub> laser MOPA system has been developed.
  - ✓ Output Power: **8 kW**
  - ✓ Pulse Width: 20 ns
  - ✓ Repetition Rate: 100 kHz
  - ✓ Beam propagation factor M2 : 1.1
- Short-Pulse Amplification Performance
  - ✓ Amplification performance of the MOPA system has been evaluated.
  - ✓ There is no significant wavefront distortion by amplification.
- EUV generation from high power CO<sub>2</sub> laser produced Sn plasma
  - ✓ IF EUV power **60 W** (4 sr, calculated), 16 W (measured by π sr, 1/3 angle collector)
- Next Step
  - ✓ For 20 kW output power
    - Increase the filling factor for effective amplification.
    - Evaluate the laser damage threshold of the optics.

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